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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
<u>V_h</u>	Yamamichi et al., "An ECR MOCVD (Ba,Sr)TiO ₃ Based Stacked Capacitor Technology with RuO ₂ /Ru/TiN/TiSi _x Storage Nodes for Gbit-Scale DRAMs," IEDM Technical Digest, pp. 119-112, December 1995.						
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